

ABSTRACT OF THE DISCLOSURE

The invention a chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer having a varied concentration of barium and strontium, and/or titanium, within the layer. A substrate is positioned within a chemical vapor deposition reactor. Barium and strontium are provided within the reactor by flowing at least one metal organic precursor to the reactor. Titanium is provided within the reactor. One or more oxidizers are flowed to the reactor. In one aspect, conditions are provided within the reactor to be effective to deposit a barium strontium titanate comprising dielectric layer on the substrate from the reactants.